

DESCRIPTION

FEATURES

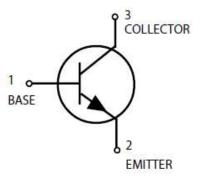
The BC817-40W is available in SC-70 Package.

Available in SC-70 Package.

ORDERING INFORMATION

Package Type	Part Number		
SC-70	BC817-40W		
Note SPQ: 3,000pcs/Reel			
AiT provides all RoHS Compliant Products			

PIN DESCRIPTION



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ABSOLUTE MAXIMUM RATINGS

V _{CEO} , Collector–Emitter Voltage	45V
V _{CBO} , Collector–Base Voltage	50V
V _{EBO} , Emitter–Base Voltage	5.0V
I _C , Collector Current — Continuous	500mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max.	Unit
Total Device Dissipation FR-5 BoardNOTE1			
T _A = 25°C	P_{D}	150	mW
Derate above 25°C		1.2	mW/°C
Thermal Resistance, Junction to Ambient	Reja	833	°C/W
Total Device Dissipation Alumina SubstrateNOTE2			
T _A = 25°C	P_{D}	200	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance, Junction to Ambient	Reja	625	°C/W
Junction and Storage Temperature	T _J , T _{STG}	-55 to +150	°C

NOTE1: FR-5 = 1.0 x 0.75 x 0.062 in.

NOTE2: Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

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ELECTRICAL CHARACTERISTICS

T_A = 25°C unless otherwise noted

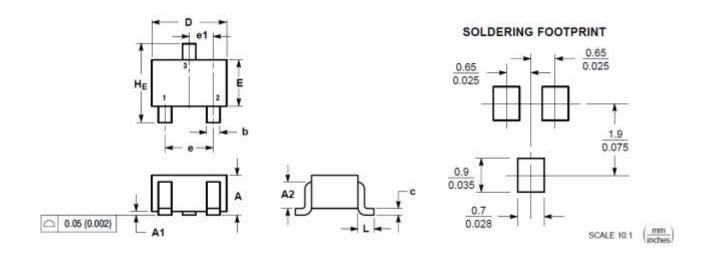
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage	V _{(BR)CEO} I _C = 10mA		45	-	-	V
Collector–Emitter Breakdown Voltage	V _{(BR)CES}	$V_{EB} = 0$, $I_{C} = 10\mu A$	50	-	-	V
Emitter–Base Breakdown Voltage	V _{(BR)EBO}) I _E = 1.0μA		-	-	V
	Ісво	V _{CB} = 20V	-	-	100	nA
Collector Cutoff Current		V _{CB} = 20V, T _A = 150°C	-	-	5.0	μΑ
ON CHARACTERISTICS						
DC Current Gain	h _{FE}	I _C = 100mA, V _{CE} = 1.0V	250	-	600	-
		I _C = 500mA, V _{CE} = 1.0V	40	-	-	
Collector–Emitter Saturation Voltage	V _{CE(sat)}	I _C = 500mA, I _B = 50mA		-	0.7	V
Base–Emitter On Voltage	V _{BE(ON)} I _C = 500mA, V _{CE} = 1.0V		-	-	1.2	V
SMALL-SIGNAL CHARACTERISTICS						
Current–Gain — Bandwidth Product	f⊤	I _C = 10mA, V _{CE} = 5.0Vdc,	400			N 41 1—
		f = 100MHz	100 -		-	MHz
Output Capacitance	C _{obo}	V _{CB} = 10V, f = 1.0MHz	-	10	-	рF

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PACKAGE INFORMATION

Dimension in SC-70 Package (Unit: mm)



DIM	MILLIN	METERS	INCHES		
	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.032	0.040	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.70 REF 0.028 REF		REF	
b	0.30	0.40	0.012	0.016	
С	0.10	0.25	0.004	0.010	
D	1.80	2.20	0.071	0.087	
Е	1.15	1.35	0.045	0.053	
е	1.20	1.40	0.047	0.055	
e1	0.65 BSC		0.026 BSC		
L	0.425 REF		0.017	REF	
HE	2.00	2.40	0.079	0.095	

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